

MOSFETs Silicon P-Channel MOS

### SSM6P49NU

#### 1. Applications

· Power Management Switches

#### 2. Features

- (1) 1.8 V drive
- (2) Low drain-source on-resistance

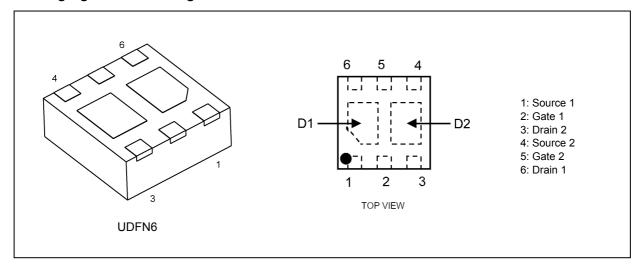
 $: R_{DS(ON)} = 157 \text{ m}\Omega \text{ (max) } (@V_{GS} = -1.8 \text{ V})$ 

 $R_{\rm DS(ON)}$  = 76 m $\Omega$  (max) (@V<sub>GS</sub> = -2.5 V)

 $R_{DS(ON)} = 56 \text{ m}\Omega \text{ (max) (@V_{GS} = -4.5 V)}$ 

 $R_{\mathrm{DS(ON)}} = 45~\mathrm{m}\Omega~(\mathrm{max})~(@V_{\mathrm{GS}} = -10~\mathrm{V})$ 

#### 3. Packaging and Pin Assignment



1



#### Absolute Maximum Ratings (Note) (Unless otherwise specified, T<sub>a</sub> = 25 °C)(Q1, Q2 Common)

	Characteristics		Symbol	Rating	Unit
Drain-source voltage			$V_{DSS}$	-20	V
Gate-source voltage			V <sub>GSS</sub>	±12	
Drain current (DC)		(Note 1)	I <sub>D</sub>	-4	Α
Drain current (pulsed)		(Note 1), (Note 2	?) I <sub>DP</sub>	-16	
Power dissipation		(Note 3)	P <sub>D</sub>	1	W
Power dissipation	(t ≤ 10 :	s) (Note 3)		2	
Channel temperature			T <sub>ch</sub>	150	°C
Storage temperature			T <sub>stg</sub>	-55 to 150	

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

- Note 1: Ensure that the channel temperature does not exceed 150 °C.
- Note 2: Pulse width (PW)  $\leq$  100  $\mu$ s, duty  $\leq$  1 %
- Note 3: Device mounted on a FR4 board. (25.4 mm × 25.4 mm × 1.6 mm, Cu pad: 645 mm<sup>2</sup>)

Note: This transistor is sensitive to electrostatic discharge and should be handled with care.

Note: The MOSFETs in this device are sensitive to electrostatic discharge. When handling this device, the worktables, operators, soldering irons and other objects should be protected against anti-static discharge.

Note: The channel-to-ambient thermal resistance, R<sub>th(ch-a)</sub>, and the drain power dissipation, P<sub>D</sub>, vary according to the board material, board area, board thickness and pad area. When using this device, be sure to take heat dissipation fully into account.

#### 5. Thermal Characteristics

Characteristics		Symbol	Max	Unit
Channel-to-ambient thermal resistance (Note 1)		R <sub>th(ch-a)</sub>	125	°C/W

Note 1: Device mounted on an 25.4 mm × 25.4 mm × 1.6 mm FR4 glass epoxy board (Cu pad: 645 mm<sup>2</sup>)



#### 6. Electrical Characteristics

# 6.1. Static Characteristics (Unless otherwise specified, T<sub>a</sub> = 25 °C)(Q1, Q2 Common)

Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current		I <sub>GSS</sub>	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 10 \text{ V}$	_	_	±1	μА
Drain cut-off current		I <sub>DSS</sub>	V <sub>DS</sub> = -20 V, V <sub>GS</sub> = 0 V	_	_	-1	
Drain-source breakdown voltage		V <sub>(BR)DSS</sub>	I <sub>D</sub> = -1 mA, V <sub>GS</sub> = 0 V	-20	_	_	V
Drain-source breakdown voltage	(Note 1)	V <sub>(BR)DSX</sub>	I <sub>D</sub> = -1 mA, V <sub>GS</sub> = 8 V	-12	_	_	
Gate threshold voltage	(Note 2)	V <sub>th</sub>	$V_{DS} = -3 \text{ V}, I_{D} = -1 \text{ mA}$	-0.5	_	-1.2	
Drain-source on-resistance	(Note 3)	R <sub>DS(ON)</sub>	I <sub>D</sub> = -0.5 A, V <sub>GS</sub> = -1.8 V	_	83	157	mΩ
			I <sub>D</sub> = -2.0 A, V <sub>GS</sub> = -2.5 V	_	60	76	
			I <sub>D</sub> = -3.0 A, V <sub>GS</sub> = -4.5 V	_	44	56	
			I <sub>D</sub> = -3.5 A, V <sub>GS</sub> = -10 V	_	36	45	
Forward transfer admittance	(Note 3)	Y <sub>fs</sub>	$V_{DS} = -3 \text{ V}, I_{D} = -2.0 \text{ A}$	4.7	9.5	1	S

Note 1: If a forward bias is applied between gate and source, this device enters  $V_{(BR)DSX}$  mode. Note that the drain-source breakdown voltage is lowered in this mode.

Note 2: Let  $V_{th}$  be the voltage applied between gate and source that causes the drain current ( $I_D$ ) to below (-1 mA for this device). Then, for normal switching operation,  $V_{GS(ON)}$  must be higher than  $V_{th}$ , and  $V_{GS(OFF)}$  must be lower than  $V_{th}$ . This relationship can be expressed as:  $V_{GS(OFF)} < V_{th} < V_{GS(ON)}$ .

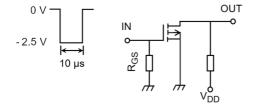
Take this into consideration when using the device.

Note 3: Pulse measurement.

### 6.2. Dynamic Characteristics (Unless otherwise specified, T<sub>a</sub> = 25 °C)(Q1, Q2 Common)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Input capacitance	C <sub>iss</sub>	$V_{DS} = -10 \text{ V}$ , $V_{GS} = 0 \text{ V}$ ,	_	480		pF
Reverse transfer capacitance	C <sub>rss</sub>	f = 1 MHz	_	76		
Output capacitance	C <sub>oss</sub>		_	90		
Switching time (turn-on time)	t <sub>on</sub>	$V_{DD}$ = -10 V, $I_{D}$ = -0.5 A, $V_{GS}$ = 0 to -2.5 V, $R_{GS}$ = 4.7 $\Omega$ ,		21	1	ns
Switching time (turn-off time)	t <sub>off</sub>	Duty $\leq$ 1 %,V <sub>IN</sub> : t <sub>r</sub> , t <sub>f</sub> < 5 ns, Common source, See Chapter 6.3.	_	54	_	

#### 6.3. Switching Time Test Circuit



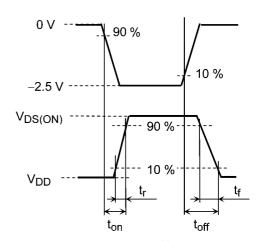


Fig. 6.3.1 Switching Time Test Circuit

Fig. 6.3.2 Input Waveform/Output Waveform



# 6.4. Gate Charge Characteristics (Unless otherwise specified, T<sub>a</sub> = 25 °C)(Q1, Q2 Common)

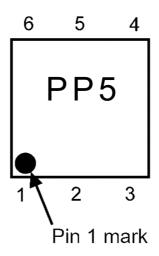
Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Total gate charge (gate-source plus gate-drain)	Qg	$V_{DD} = -10 \text{ V}, I_{D} = -4.0 \text{ A},$	_	6.74	_	nC
Gate-source charge 1	Q <sub>gs1</sub>	$V_{GS} = -4.5 \text{ V}$	_	0.95		
Gate-drain charge	Q <sub>gd</sub>		_	1.50	_	

# 6.5. Source-Drain Characteristics (Unless otherwise specified, T<sub>a</sub> = 25 °C)(Q1, Q2 Common)

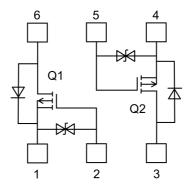
Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Diode forward voltage (Not	e 1) V <sub>DSF</sub>	I <sub>DR</sub> = 4.0 A, V <sub>GS</sub> = 0 V	_	0.87	1.2	V

Note 1: Pulse measurement.

#### 7. Marking



### 8. Internal Equivalent Circuit





#### 9. Characteristics Curves (Q1, Q2 Common) (Note)

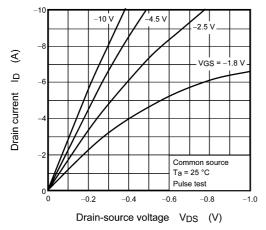
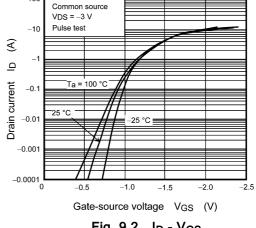


Fig. 9.1 I<sub>D</sub> - V<sub>DS</sub>



-100

Fig. 9.2 I<sub>D</sub> - V<sub>GS</sub>

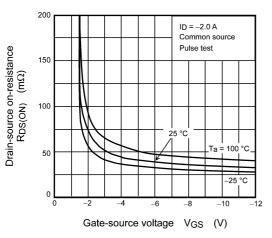


Fig. 9.3 R<sub>DS(ON)</sub> - V<sub>GS</sub>

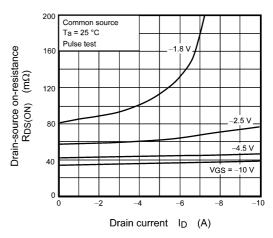


Fig. 9.4 R<sub>DS(ON)</sub> - I<sub>D</sub>

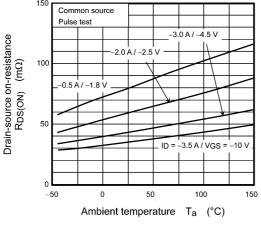


Fig. 9.5 R<sub>DS(ON)</sub> - T<sub>a</sub>

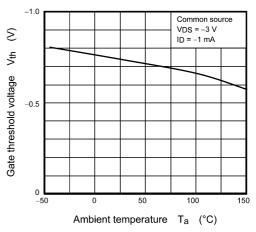


Fig. 9.6 Vth - Ta



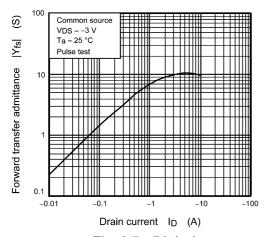


Fig. 9.7 |Y<sub>fs</sub>| - I<sub>D</sub>

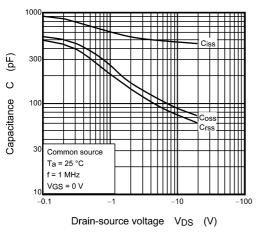


Fig. 9.9 C - V<sub>DS</sub>

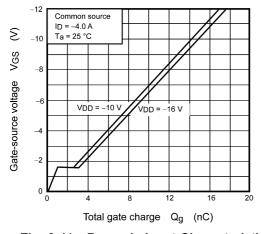


Fig. 9.11 Dynamic Input Characteristics

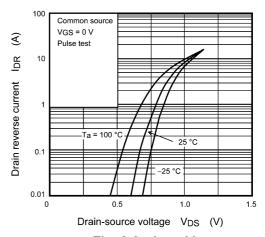


Fig. 9.8 IDR - VDS

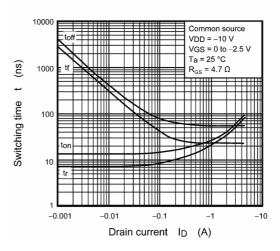


Fig. 9.10 t - I<sub>D</sub>

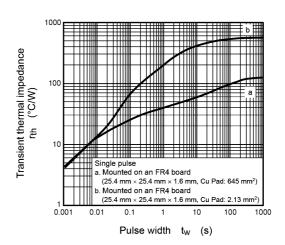
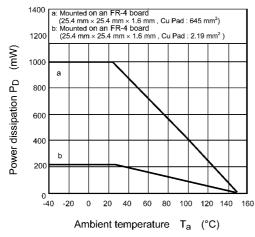


Fig. 9.12 rth - tw





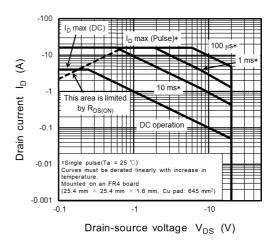


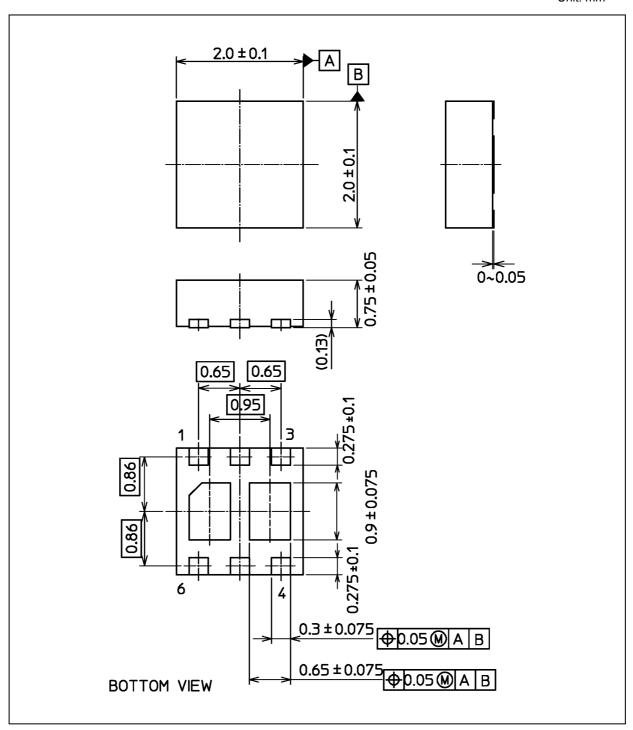
Fig. 9.13 P<sub>D</sub> - T<sub>a</sub> Fig. 9.14 Safe Operating Area

Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.



#### **Package Dimensions**

Unit: mm



Weight: 8.5 mg (typ.)

	Package Name(s)
JEDEC: SOT-1118	
Nickname: UDFN6	



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